Analog Power

N-Channel 60-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODU	ICT SUM	MARY		
V _{DS} (V)	r _{DS(0}	$m(\Omega)$	I _D (A)	
60	22 @ `	$V_{GS} = 10V$	11	
60	26 @ \	$V_{\rm GS} = 4.5 \rm V$	10	
	Top 1 2 3 3	<3-8PP View 8 □ D 7 □ D 6 □ D 5 □ D	G o	

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C U	NLESS OT	HERWIS	SE NOTED)
Parame te r		Symbol	Limit	Units
Drain-Source Voltage		V _{DS}	60	v
Gate-Source Voltage		V _{GS}	±20	V
	T _A =25°C	Τ_	±11	
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	±8	А
Pulsed Drain Current ^b		I _{DM}	±75	
Continuous Source Current (Diode Conduction) ^a		Is	16	А
Down Discinction ^a	T _A =25°C	D_	3.5	w
Power Dissipation ^a	$\begin{array}{c c} T_{A}=25^{\circ}C \\ \hline T_{A}=70^{\circ}C \end{array} P_{D} \end{array} \begin{array}{c} 3.5 \\ \hline 2 \end{array}$		••	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATIN	GS			
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{\theta JC}$	25	°C/W
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{\theta JA}$	50	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits			I Init		
Farameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = 20 V$			±100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 48 V, V_{GS} = 0 V$			1	11 A		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	20			А		
Drain-Source On-Resistance ^A		$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$			22	mΩ		
Dram-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$			26	1115.2		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$		40		S		
Diode Forward Voltage	V _{SD}	$I_{s} = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V		
Dynamic ^b								
Total Gate Charge	Qg	X = 15 X X = 45 X		28		nC		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 10 \text{ A}$		13				
Gate-Drain Charge	Q _{gd}	$I_D = 10 \text{ A}$		6				
Turn-On Delay Time	t _{d(on)}			6				
Rise Time	t _r	$V_{\rm DD}$ = 25 V, $R_{\rm L}$ = 25 Ω , ID = 1 A,		2		nS		
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 V$		24				
Fall-Time	t _f			2				

Notes

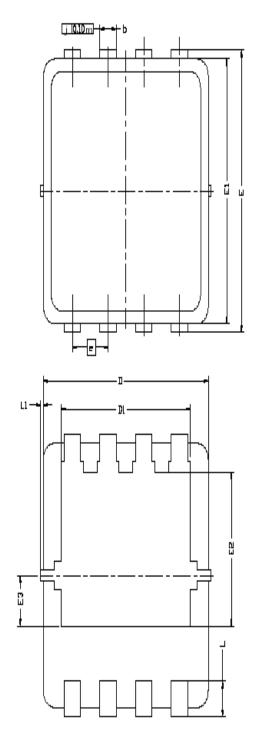
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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DIM	MIN	NDM	MAX	MIN	NDM	MAX
ĥ	0,700	0,80	0,900	0.0276	0,0315	M324
ÅL	D, QQ		D.05	Q, QQ (0.002
b	0.24	0.30	0.35	0.009	0.012	0.D14
Γ	0,10	D.152	0,25	0.004	0.006	0.010
)	3.00 BSC		0.118 BSC			
	2.35 BSC		0.093 BSC			
Ŀ	320 BSC		D126 BSC			
EL	3.00 BSC		0.118 BIC			
65	1.75 BSC		0.069 BSC			
[]	0.575 BSC		0.023 BSC			
6	0.65 BSC		0.026 BSC			
L	0.30	0.40	D20	0.0118	0.0157	0.0197
	D		Q.100	D		0.004
81	D*	10*	12'	D •	10*	12'